## 1 Scope

The present specifications shall apply to Sanken silicon diode, RM1Z.

## 2 Outline

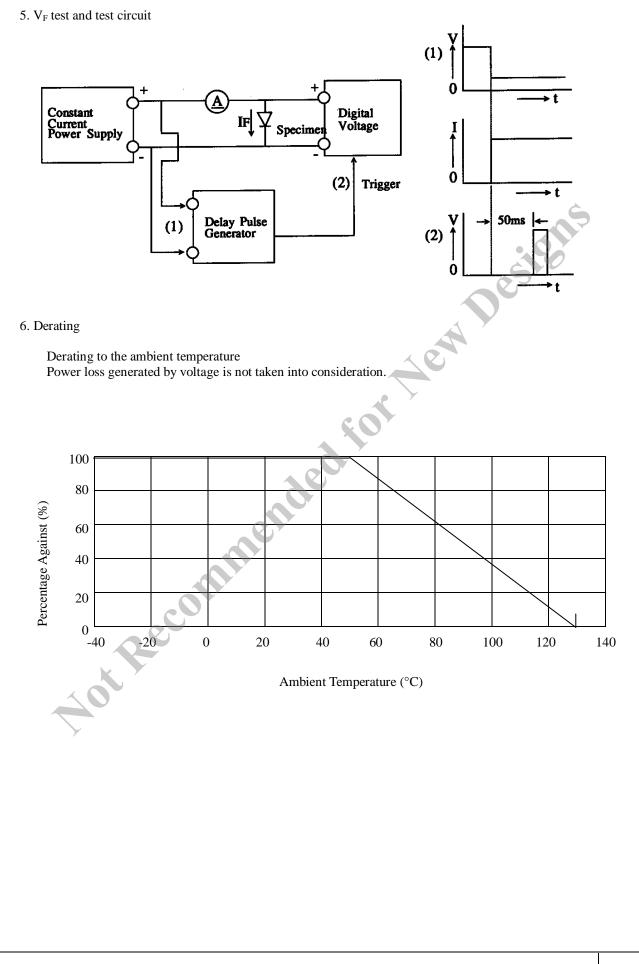
Туре	Silicon Rectifier Diode (Mesa type)				
Structure	Resin Molded Flammability: UL94V-0 (Equivalent)				
Applications	Frequency Rectification, etc.				

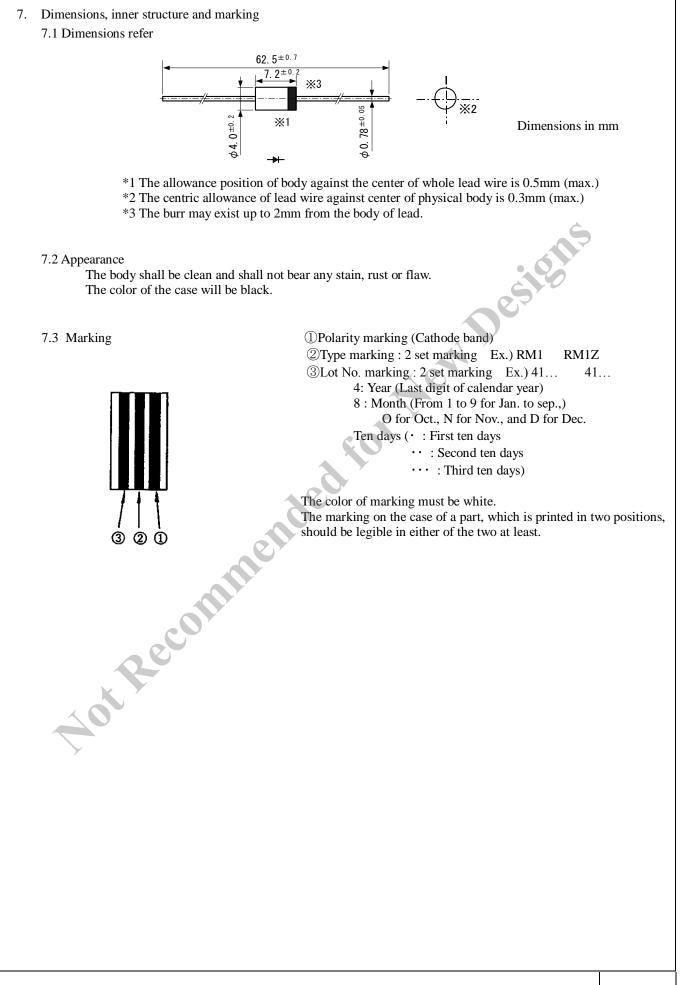
## 3 Absolute maximum ratings

8-						
No.	Item	Symbol	Unit	Rating	Conditions	
1	Transient Peak Reverse Voltage	V <sub>RSM</sub>	V	250		
2	Peak Reverse Voltage	V <sub>RM</sub>	V	200		
3	Average Forward Current	I <sub>F(AV)</sub>	А	1.0	Refer to derating curve in Section 6	
4	Peak Surge Forward Current	I <sub>FSM</sub>	А	50	50Hz. Half sinewave, one	
5	Junction Temperature	Tj	°C	-40 to +150		
6	Storage Temperature	T <sub>stg</sub>	°C	-40 to +150		

## 4 Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	$V_{\rm F}$	V	0.95 max.	I <sub>F</sub> =1.0A
2	Reverse Leakage Current	I <sub>R</sub>	μΑ	5 max.	V <sub>R</sub> =V <sub>RM</sub>
3	3 Reverse Leakage Current Under High Temperature		μΑ	50 max.	$V_R = V_{RM}, T_j = 100^{\circ}C$
4	Thermal Resistance	R <sub>th(j-l)</sub>	°C/W	15 max.	Between Junction and Lead





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